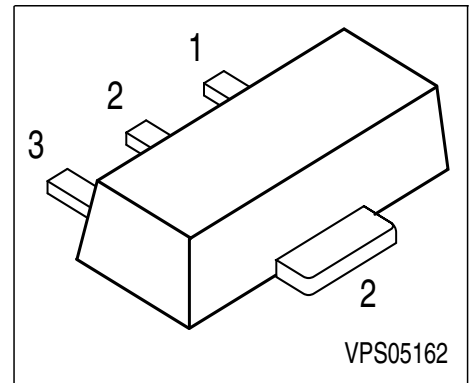


**NPN Silicon RF Transistor**

- For low noise, high-gain amplifiers up to 2 GHz
- For linear broadband amplifiers
- $f_T = 7.5$  GHz  
 $F = 1.3$  dB at 900 MHz



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFQ 193	RC	1 = B	2 = C	3 = E	SOT-89

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	12	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	2	
Collector current	$I_C$	80	mA
Base current	$I_B$	10	
Total power dissipation, $T_S \leq 93$ °C <sup>1)</sup>	$P_{tot}$	600	mW
Junction temperature	$T_j$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Junction - soldering point	$R_{thJS}$	$\leq 95$	K/W
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<sup>1)</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	100	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	1	$\mu\text{A}$
DC current gain $I_C = 30 \text{ mA}, V_{CE} = 8 \text{ V}$	$h_{FE}$	50	100	200	-

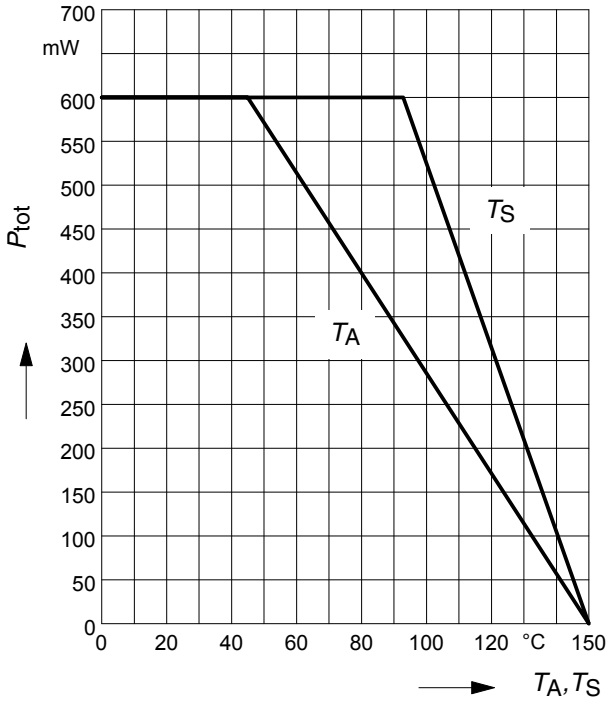
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC characteristics</b> (verified by random sampling)					
Transition frequency $I_C = 50\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 500\text{ MHz}$	$f_T$	5.5	7.5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{cb}$	-	0.78	1.2	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ce}$	-	0.36	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$	$C_{eb}$	-	2.1	-	
Noise figure $I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{\text{Sopt}}$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$F$	-	1.3 2.1	-	dB
Power gain, maximum available <sup>F)</sup> $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{\text{Sopt}}$ , $Z_L = Z_{\text{Lopt}}$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$G_{\text{ma}}$	-	14 8	-	
Transducer gain $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	-	11.5 6	-	

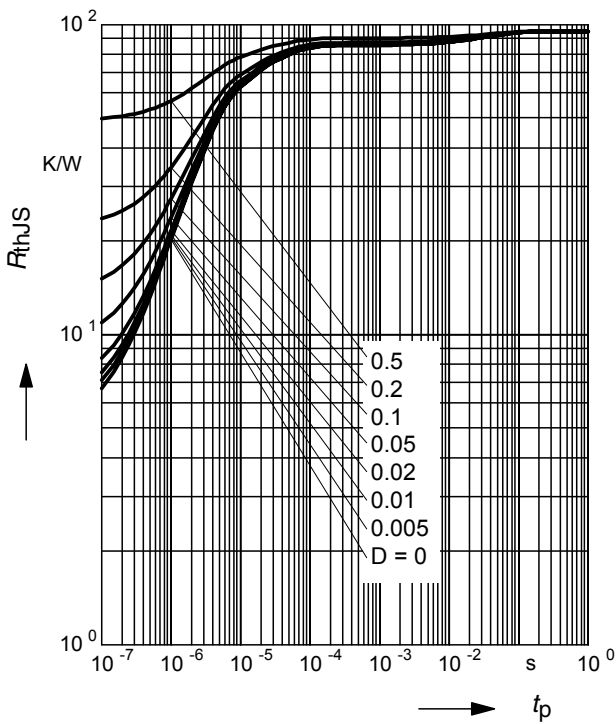
$$^1G_{\text{ma}} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

**Total power dissipation  $P_{tot} = f(T_A^*, T_S)$**

\* Package mounted on epoxy



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$

